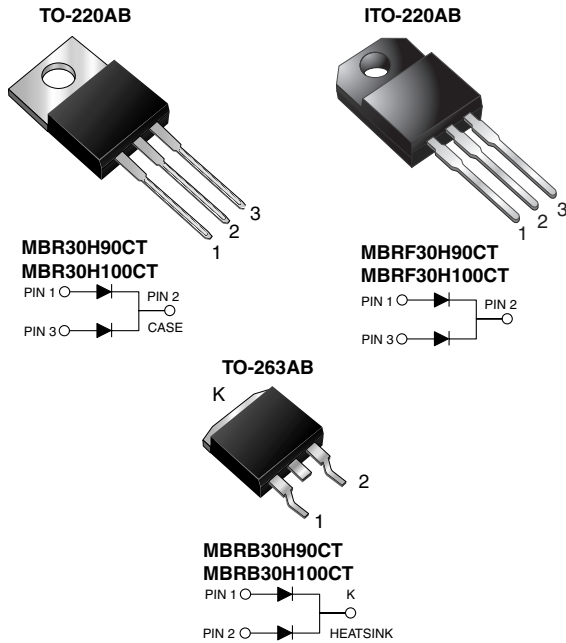




Dual Common-Cathode High-Voltage Schottky Rectifier

High Barrier Technology for Improved High Temperature Performance



FEATURES

- Guardring for overvoltage protection
- Lower power losses, high efficiency
- Low forward voltage drop
- Low leakage current
- High forward surge capability
- High frequency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder dip 260 °C, 40 s (for TO-220AB and ITO-220AB package)
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
 COMPLIANT

TYPICAL APPLICATIONS

For use in high frequency rectifier of switching mode power supplies, freewheeling diodes, dc-to-dc converters or polarity protection application.

MECHANICAL DATA

Case: TO-220AB, ITO-220AB, TO-263AB

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test, HE3 suffix for high reliability grade (AEC Q101 qualified), meets JESD 201 class 2 whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

PRIMARY CHARACTERISTICS	
$I_{F(AV)}$	15 A x 2
V_{RRM}	90 V, 100 V
I_{FSM}	275 A
V_F	0.67 V
I_R	5.0 μ A
$T_J \text{ max.}$	175 °C

MAXIMUM RATINGS ($T_C = 25 \text{ }^\circ\text{C}$ unless otherwise noted)				
PARAMETER	SYMBOL	MBR30H90CT	MBR30H100CT	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	90	100	V
Working peak reverse voltage	V_{RWM}	90	100	V
Maximum DC blocking voltage	V_{DC}	90	100	V
Maximum average forward rectified current (Fig. 1)	$I_{F(AV)}$	30 15		A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I_{FSM}	275		A
Peak repetitive reverse current per diode at $t_p = 2 \text{ } \mu\text{s}$, 1 kHz	I_{RRM}	1.0		A
Voltage rate of change (rated V_R)	dV/dt	10 000		V/ μ s
Operating junction and storage temperature range	T_J, T_{STG}	- 65 to + 175		°C
Isolation voltage (ITO-220AB only) from terminal to heatsink $t = 1 \text{ min}$	V_{AC}	1500		V

New Product

MBR(F,B)30H90CT & MBR(F,B)30H100CT



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ELECTRICAL CHARACTERISTICS ($T_C = 25\text{ }^\circ\text{C}$ unless otherwise noted)					
PARAMETER	TEST CONDITIONS		SYMBOL	VALUE	UNIT
Maximum instantaneous forward voltage per diode ⁽¹⁾	$I_F = 15\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$	V_F	0.82	V
	$I_F = 15\text{ A}$	$T_J = 125\text{ }^\circ\text{C}$		0.67	
	$I_F = 30\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$		0.93	
	$I_F = 30\text{ A}$	$T_J = 125\text{ }^\circ\text{C}$		0.80	
Maximum reverse current at rated V_R per diode ⁽²⁾		$T_J = 25\text{ }^\circ\text{C}$ $T_J = 125\text{ }^\circ\text{C}$	I_R	5.0 6.0	μA mA

Notes:

- (1) Pulse test: 300 μs pulse width, 1 % duty cycle
- (2) Pulse test: Pulse width $\leq 40\text{ ms}$

THERMAL CHARACTERISTICS ($T_C = 25\text{ }^\circ\text{C}$ unless otherwise noted)					
PARAMETER	SYMBOL	MBR	MBRF	MBRB	UNIT
Typical thermal resistance per diode	$R_{\theta JC}$	1.9	4.6	1.9	$^\circ\text{C/W}$

ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-220AB	MBR30H100CT-E3/45	1.85	45	50/tube	Tube
ITO-220AB	MBRF30H100CT-E3/45	1.99	45	50/tube	Tube
TO-263AB	MBRB30H100CT-E3/45	1.35	45	50/tube	Tube
TO-263AB	MBRB30H100CT-E3/81	1.35	81	800/reel	Tape and reel
TO-220AB	MBR30H100CTHE3/45 ⁽¹⁾	1.85	45	50/tube	Tube
ITO-220AB	MBRF30H100CTHE3/45 ⁽¹⁾	1.99	45	50/tube	Tube
TO-263AB	MBRB30H100CTHE3/45 ⁽¹⁾	1.35	45	50/tube	Tube
TO-263AB	MBRB30H100CTHE3/81 ⁽¹⁾	1.35	81	800/reel	Tape and reel

Note:

- (1) Automotive grade AEC Q101 qualified

RATINGS AND CHARACTERISTICS CURVES

($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

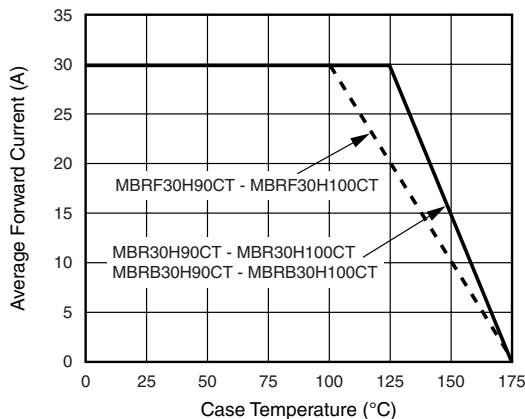


Figure 1. Forward Derating Curve Per Diode

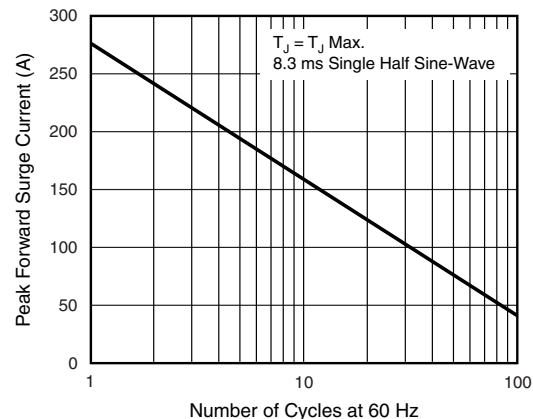


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode



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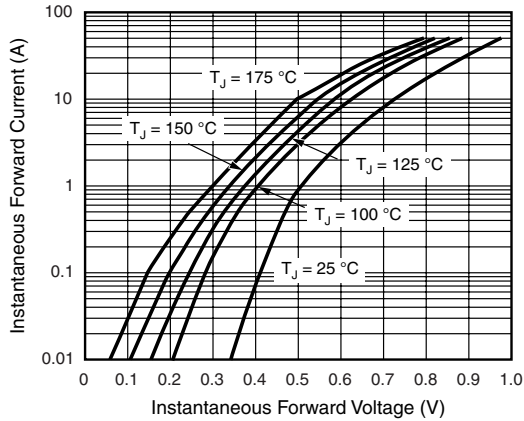


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

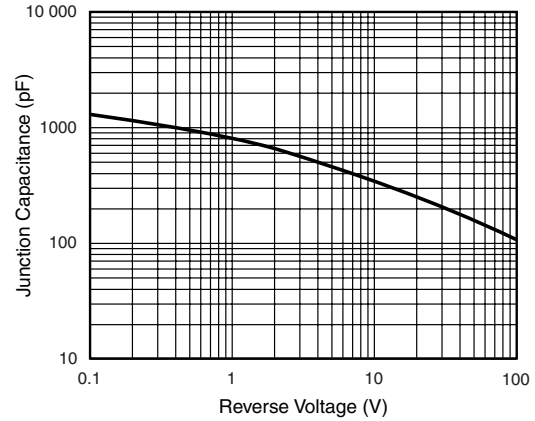


Figure 5. Typical Junction Capacitance Per Diode

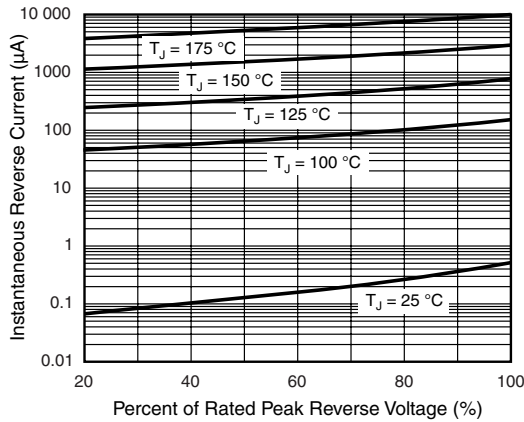


Figure 4. Typical Reverse Characteristics Per Diode

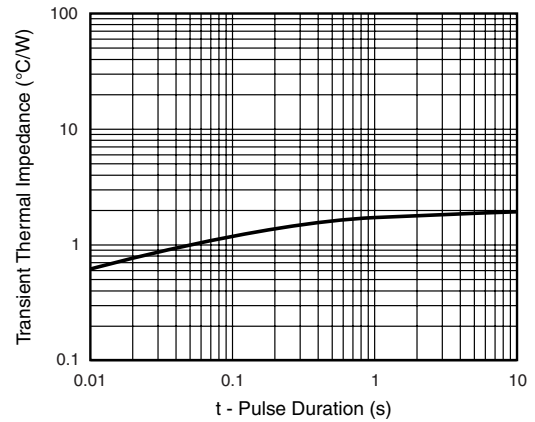


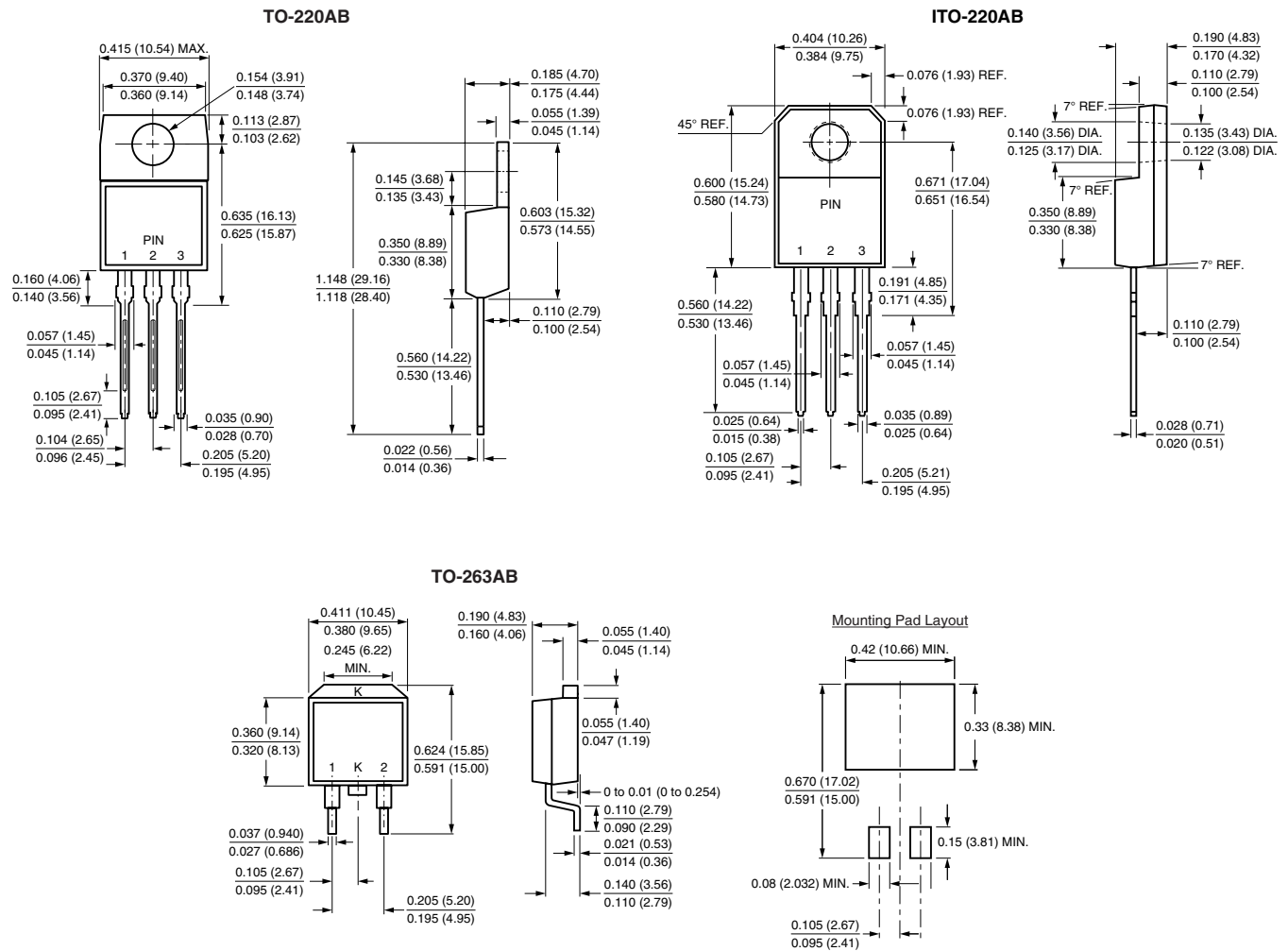
Figure 6. Typical Transient Thermal Impedance Per Diode

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PACKAGE OUTLINE DIMENSIONS in inches (millimeters)





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